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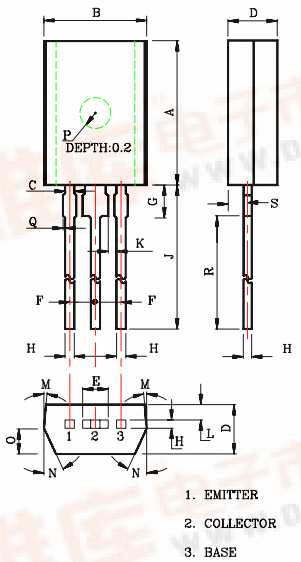
KEL
KOREA ELECTRONICS CO.,LTD.

# SEMICONDUCTOR
TECHNICAL DATA

# KTC1006
EPITAXIAL PLANAR NPN TRANSISTOR

CB TRANSCEIVER TX DRIVER APPLICATION.

## FEATURES
- Recommended for Driver Stage Application of AM 4W Transmitter.
- High Power Gain.
- Wide Area of Safe Operation.




| DIM | MILLIMETERS |
|---|---|
| A | 7.20 MAX |
| B | 5.20 MAX |
| C | 0.60 MAX |
| D | 2.50 MAX |
| E | 1.15 MAX |
| F | 1.27 |
| G | 1.70 MAX |
| H | 0.55 MAX |
| J | 14.00±0.50 |
| K | 0.35 MIN |
| L | 0.75±0.10 |
| M | 4° |
| N | 25° |
| O | 1.25 |
| P | ø1.50 |
| Q | 0.10 MAX |
| R | 12.50±0.50 |
| S | 1.00 |

TO-92L

## MAXIMUM RATINGS (Ta=25℃)

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|---|---|---|---|
| Collector-Base Voltage | $V_{CBO}$ | 80 | V |
| Collector-Emitter Voltage | $V_{CER}$ | 80 | V |
| Emitter-Base Voltage | $V_{EBO}$ | 5 | V |
| Collector Current | $I_C$ | 800 | mA |
| Emitter Current | $I_E$ | -800 | mA |
| Colletor Power Dissipation | $P_C$ | 1 | W |
| Junction Temperature | $T_j$ | 150 | ℃ |
| Storage Temperature Range | $T_{stg}$ | -55～150 | ℃ |

## ELECTRICAL CHARACTERISTICS (Ta=25℃)

| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|---|---|---|---|---|---|---|
| Collector Cut-off Current | $I_{CBO}$ | $V_{CB}$=60V, $I_E$=0 | - | - | 0.1 | μA |
| Collector Cut-off Current | $I_{CER}$ | $V_{CE}$=80V, $R_{BE}$=220Ω | - | - | 0.1 | μA |
| Emitter Cut-off Current | $I_{EBO}$ | $V_{EB}$=5V, $I_C$=0 | - | - | 0.1 | μA |
| DC Current Gain | $h_{FE}$ | $V_{CE}$=2V, $I_C$=150mA | 100 | - | - | |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C$=500mA, $I_B$=20mA | - | - | 0.7 | V |
| Base-Emitter Voltage | $V_{BE}$ | $V_{CE}$=2V, $I_C$=500mA | - | 0.9 | - | V |
| Transition Frequency | $f_T$ | $V_{CE}$=10V, $I_C$=100mA | - | 150 | - | MHz |
| Collector Output Capacitance | $C_{ob}$ | $V_{CB}$=10V, $I_E$=0, f=1MHz | - | 12 | - | pF |

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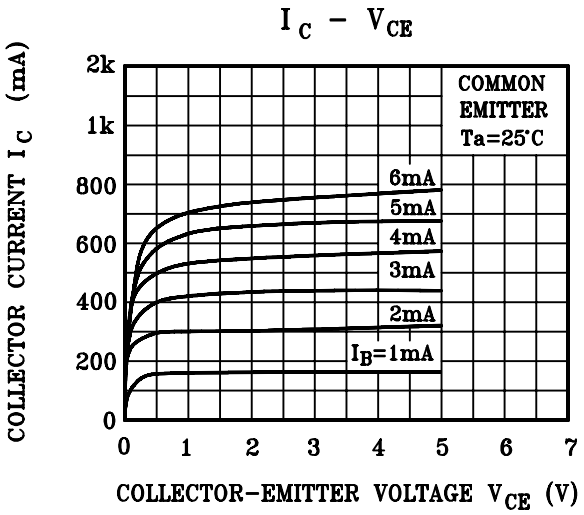
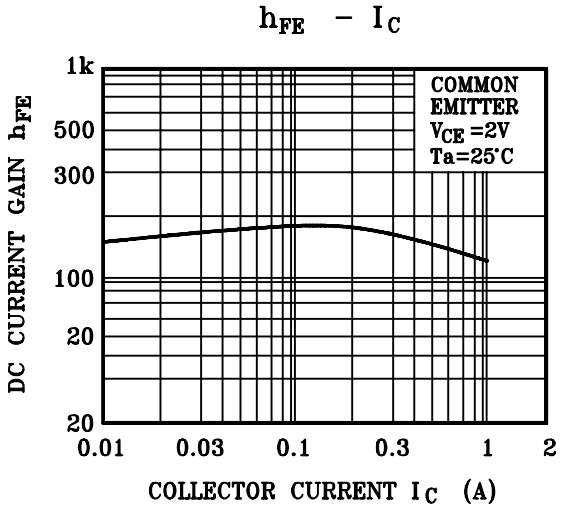
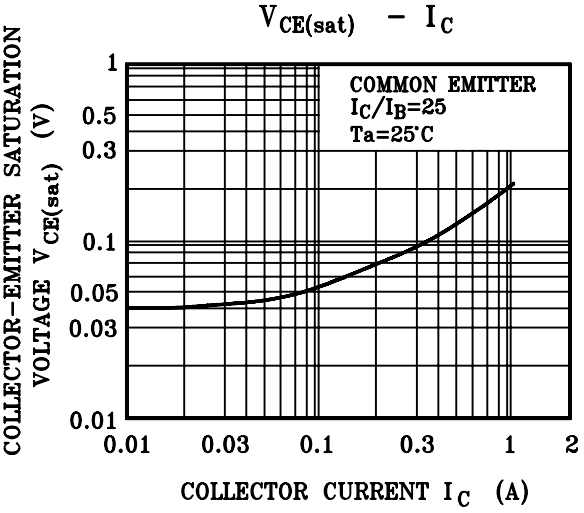
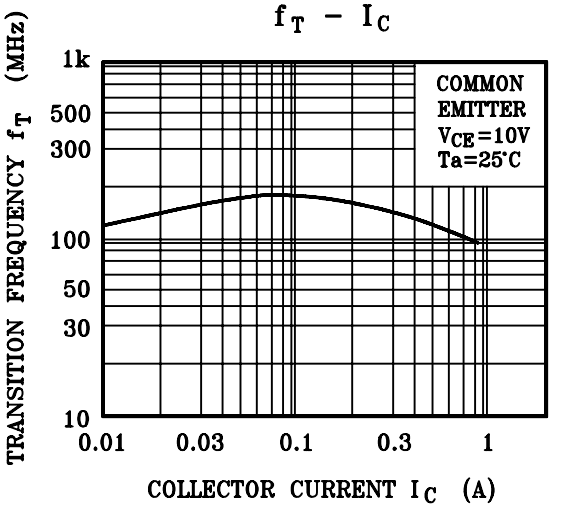
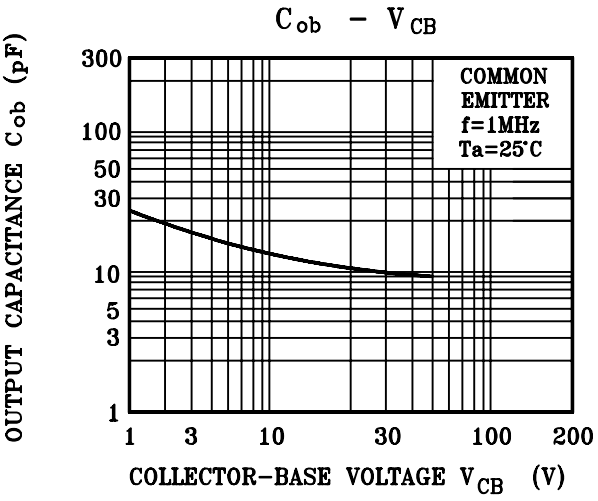
# KTC1006

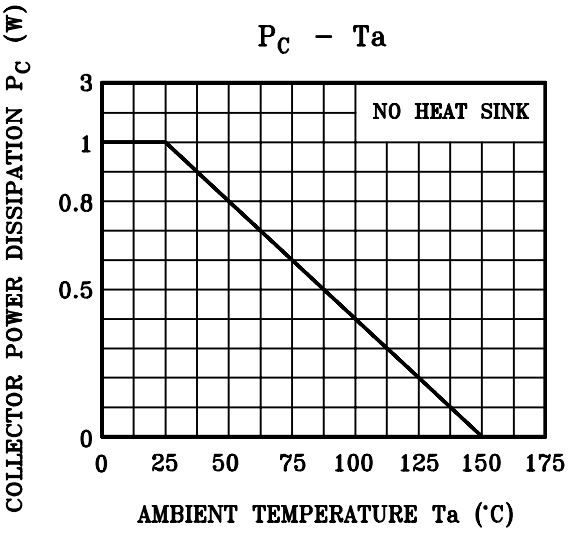

$I_C$ – $V_{CE}$
COMMON EMITTER
Ta=25°C
6mA
5mA
4mA
3mA
2mA
$I_B$=1mA
COLLECTOR CURRENT $I_C$ (mA)
COLLECTOR-EMITTER VOLTAGE $V_{CE}$ (V)


$h_{FE}$ – $I_C$
COMMON EMITTER
$V_{CE}$ =2V
Ta=25°C
DC CURRENT GAIN $h_{FE}$
COLLECTOR CURRENT $I_C$ (A)


$V_{CE(sat)}$ – $I_C$
COMMON EMITTER
$I_C/I_B$=25
Ta=25°C
COLLECTOR-EMITTER SATURATION VOLTAGE $V_{CE(sat)}$ (V)
COLLECTOR CURRENT $I_C$ (A)


$f_T$ – $I_C$
COMMON EMITTER
$V_{CE}$=10V
Ta=25°C
TRANSITION FREQUENCY $f_T$ (MHz)
COLLECTOR CURRENT $I_C$ (A)


$C_{ob}$ – $V_{CB}$
COMMON EMITTER
f=1MHz
Ta=25°C
OUTPUT CAPACITANCE $C_{ob}$ (pF)
COLLECTOR-BASE VOLTAGE $V_{CB}$ (V)


$P_C$ – Ta
NO HEAT SINK
COLLECTOR POWER DISSIPATION $P_C$ (W)
AMBIENT TEMPERATURE Ta (°C)